

Description

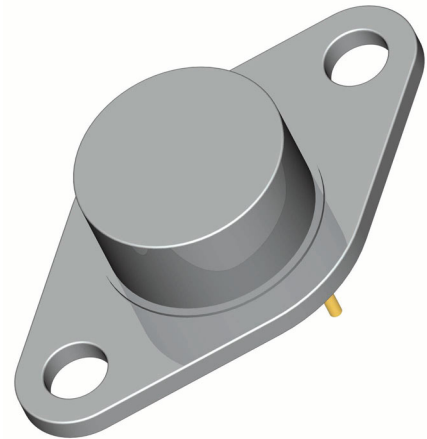
Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N5660J)
- JANTX level (2N5660JX)
- JANTXV level (2N5660JV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations
www.SEMICOA.com or (714) 979-1900

Applications

- General purpose
- Power Transistor
- NPN silicon transistor



Features

- Hermetically sealed TO-66 metal can
- Also available in chip configuration
- Chip geometry 1031
- Reference document: MIL-PRF-19500/454

Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Absolute Maximum Ratings		$T_C = 25^\circ\text{C}$ unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	200	Volts
Collector-Base Voltage	V_{CBO}	250	Volts
Emitter-Base Voltage	V_{EBO}	6	Volts
Collector Current, Continuous	I_C	2	A
Power Dissipation, $T_A = 25^\circ\text{C}$ Derate linearly above 25°C	P_T	2 11.4	W mW/ $^\circ\text{C}$
Power Dissipation, $T_C = 25^\circ\text{C}$ Derate linearly above 100°C	P_T	20 200	W mW/ $^\circ\text{C}$
Operating Junction Temperature	T_J	-65 to +200	$^\circ\text{C}$
Storage Temperature	T_{STG}		

ELECTRICAL CHARACTERISTICS

characteristics specified at $T_A = 25^\circ\text{C}$

Off Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}$	200			Volts
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	$I_C = 10 \text{ mA}, R_{BE} = 100 \Omega$	250			Volts
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10 \mu\text{A}$	6			Volts
Collector-Base Cutoff Current	I_{CBO1}	$V_{CB} = 200 \text{ Volts}$			0.1	μA
	I_{CBO2}	$V_{CB} = 250 \text{ Volts}$			1.0	mA
Collector-Emitter Cutoff Current	I_{CES1}	$V_{CE} = 200 \text{ Volts}$			0.2	μA
	I_{CES2}	$V_{CE} = 200 \text{ Volts}, T_A = 150^\circ\text{C}$			100	

On Characteristics			Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$			
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	h_{FE1}	$I_C = 50 \text{ mA}, V_{CE} = 2 \text{ Volts}$	40		120	
	h_{FE2}	$I_C = 500 \text{ mA}, V_{CE} = 5 \text{ Volts}$	40			
	h_{FE3}	$I_C = 1 \text{ A}, V_{CE} = 5 \text{ Volts}$	15			
	h_{FE4}	$I_C = 2 \text{ A}, V_{CE} = 5 \text{ Volts}$	5			
	h_{FE5}	$I_C = 500 \text{ mA}, V_{CE} = 5 \text{ Volts}$ $T_A = -55^\circ\text{C}$	15			
Base-Emitter Saturation Voltage	V_{BEsat1}	$I_C = 1 \text{ A}, I_B = 100 \text{ mA}$			1.2	Volts
	V_{BEsat2}	$I_C = 2 \text{ A}, I_B = 400 \text{ mA}$			1.5	
Collector-Emitter Saturation Voltage	V_{CEsat1}	$I_C = 1 \text{ A}, I_B = 100 \text{ mA}$			0.4	Volts
	V_{CEsat2}	$I_C = 2 \text{ A}, I_B = 400 \text{ mA}$			0.8	

Dynamic Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 5 \text{ Volts}, I_C = 100 \text{ mA}, f = 10 \text{ MHz}$	2		7	
Open Circuit Output Capacitance	C_{OBO}	$V_{CB} = 10 \text{ Volts}, I_E = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			45	pF

Switching Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Saturated Turn-On Time	t_{ON}	$I_C = 500 \text{ mA}, V_{CC} = 100 \text{ Volts}$			250	ns
Saturated Turn-Off Time	t_{OFF}	$I_C = 500 \text{ mA}, V_{CC} = 100 \text{ Volts}$			850	ns